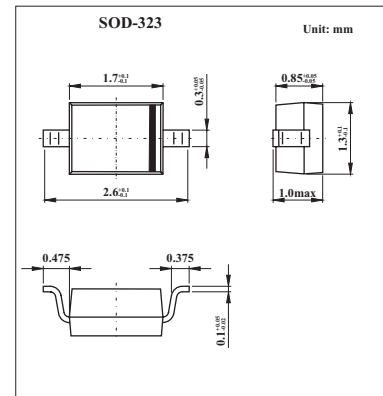


# 1PS76SB70

## ■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package
- Low diode capacitance.



## ■ Absolute Maximum Ratings Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	V <sub>R</sub>			70	V
continuous forward current	I <sub>F</sub>			70	mA
repetitive peak forward current	I <sub>FRM</sub>	t <sub>p</sub> ≤ 1 s; δ ≤ 0.5		70	mA
non-repetitive peak forward current	I <sub>FSM</sub>	t <sub>p</sub> < 10 ms		100	mA
storage temperature	T <sub>stg</sub>		-65	+150	°C
junction temperature	T <sub>j</sub>			150	°C
operating ambient temperature	T <sub>amb</sub>		-65	+150	°C

## ■ Electrical Characteristics Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MAX	UNIT
continuous forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 mA	410	mV
		I <sub>F</sub> = 10 mA	750	mV
		I <sub>F</sub> = 40 mA	1	V
continuous reverse current	I <sub>R</sub>	V <sub>R</sub> = 50 V; note 1	100	μA
		V <sub>R</sub> = 70 V; note 1	10	μA
diode capacitance	C <sub>d</sub>	V <sub>R</sub> = 0 V; f = MHz	5	pF
thermal resistance from junction to ambient	R <sub>thj-a</sub>		450	K/W

Note:

1. Pulse test: t<sub>p</sub> = 300 μs; δ = 0.02.

## ■ Marking

Marking	S2
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